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Body Length:
1.290 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
0.210 inches
Maximum Power Dissipation Rating:
1.02 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and monolithic and schottky and bipolar and programmable and programmed and positive outputs
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
13 input
Case Outline Source And Designator:
D-3 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
5.5 volts power source
Time Rating Per Chacteristic:
90.00 nanoseconds propagation delay time, low to high level output and 90.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Memory Capacity:
Unknown
Special Features:
Alter in accordance w/g.E. Drawing 77a102341p1
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification

format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain

environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

24 printed circuit

Specification Data:

813/0-mil-m-38510/208/usaf/ government specification

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N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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